IRFU15N20DPBF-VB Datasheet

N-Channel 200V (D-S) MOSFET

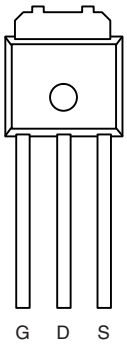
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
200	0.056 at V_{GS} = 10 V	25
	0.070 at V_{GS} = 6 V	23

FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

TO-251

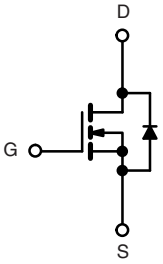


Drain Connected to Drain-Tab

Top View

APPLICATIONS

- Primary Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)[b]	T_C = 25 °C	I_D	25	A
	T_C = 125 °C		17	
Pulsed Drain Current		I_{DM}	60	
Continuous Source Current (Diode Conduction)		I_S	19	
Avalanche Current		I_{AS}	25	
Single Pulse Avalanche Energy	L = 0.1 mH	E_{AS}	18	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	145[b]	W
	T_A = 25 °C		3.5[a]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

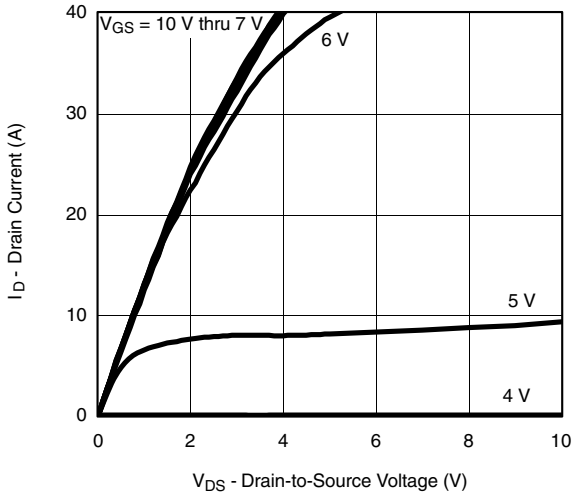
THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Junction-to-Case (Drain)		R_{thJC}	0.85	1.1	

Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. See SOA curve for voltage derating.

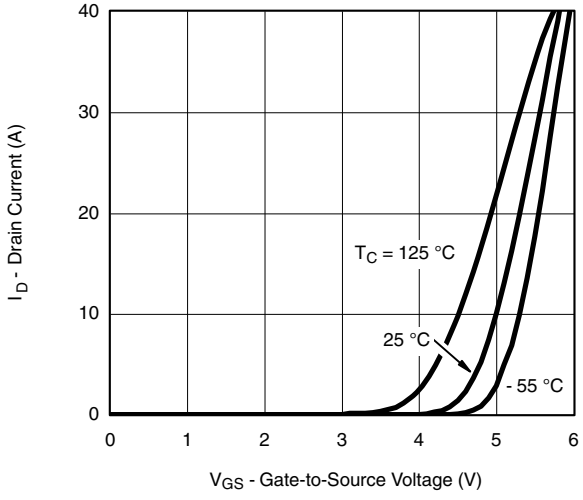
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	200			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 200 V, V_{GS} = 0 V			1	µA
		V_{DS} = 200 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 200 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	40			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 5 A		0.056		Ω
		V_{GS} = 10 V, I_D = 5 A, T_J = 125 °C		0.130		
		V_{GS} = 10 V, I_D = 5 A, T_J = 175 °C		0.260		
		V_{GS} = 6 V, I_D = 5 A		0.070		
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 19 A		35		S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, F = 1 MHz		2400		pF
Output Capacitance	C_{oss}			280		
Reverse Transfer Capacitance	C_{rss}			180		
Total Gate Charge[c]	Q_g	V_{DS} = 100 V, V_{GS} = 10 V, I_D = 19 A		40		nC
Gate-Source Charge[c]	Q_{gs}			10		
Gate-Drain Charge[c]	Q_{gd}			15		
Gate Resistance	R_g		0.5		2.9	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 100 V, R_L = 5.2 Ω I_D ≅ 19 A, V_{GEN} = 10 V, R_g = 2.5 Ω		15	25	ns
Rise Time[c]	t_r			50	75	
Turn-Off Delay Time[c]	$t_{d(off)}$			30	45	
Fall Time[c]	t_f			60	90	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)						
Pulsed Current	I_{SM}				50	A
Diode Forward Voltage[b]	V_{SD}	I_F = 19 A, V_{GS} = 0 V		0.9	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 19 A, dI/dt = 100 A/µs		180	250	ns

Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. Independent of operating temperature.

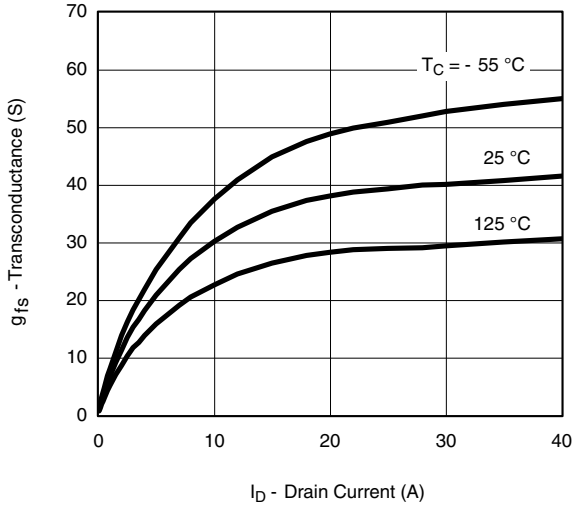
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



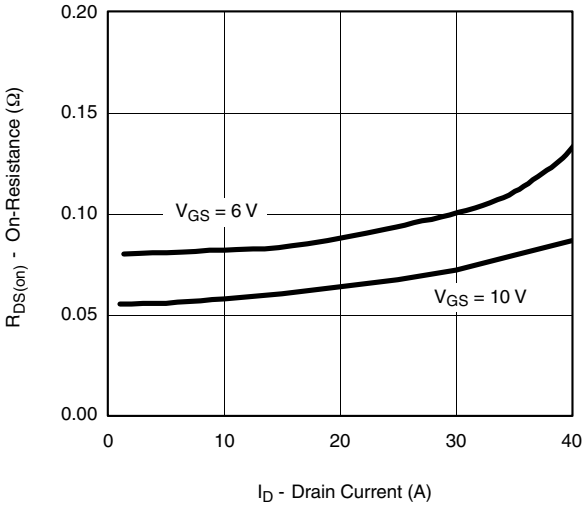
Output Characteristics



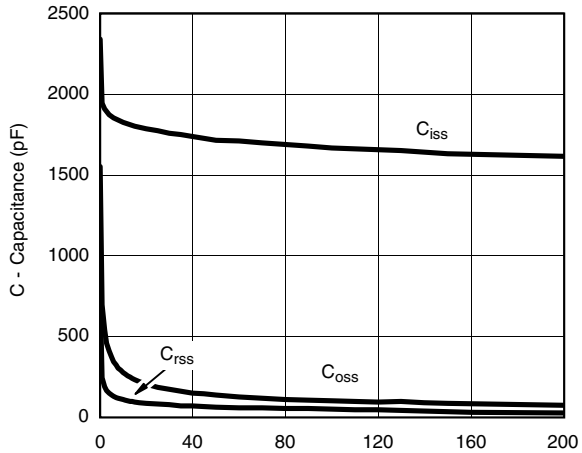
Transfer Characteristics



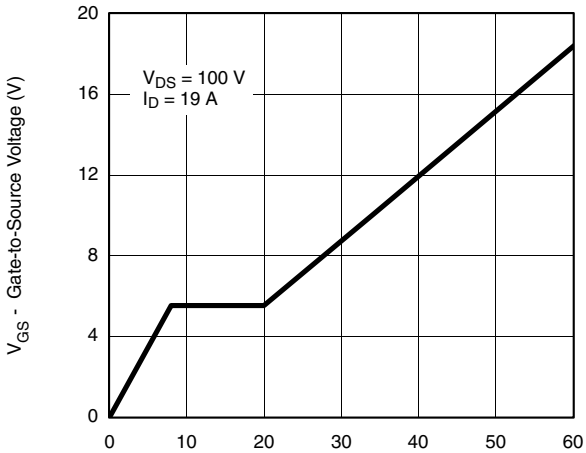
Transconductance



On-Resistance vs. Drain Current

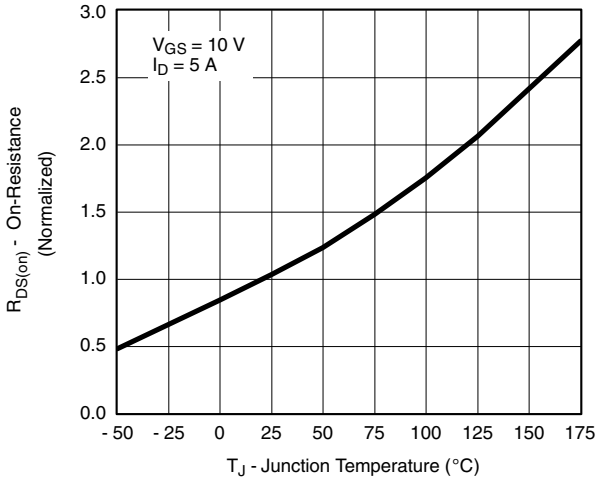


Capacitance

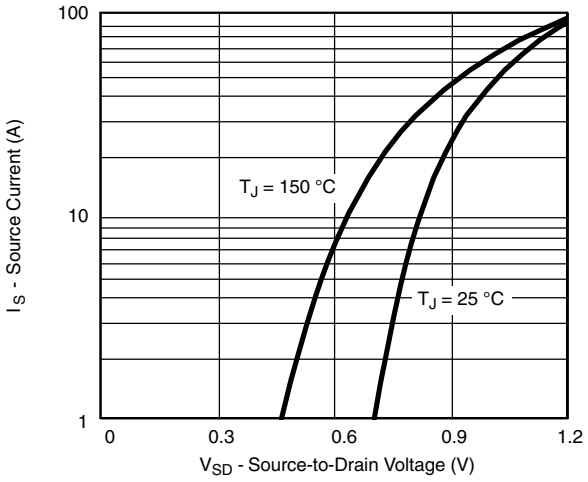


Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

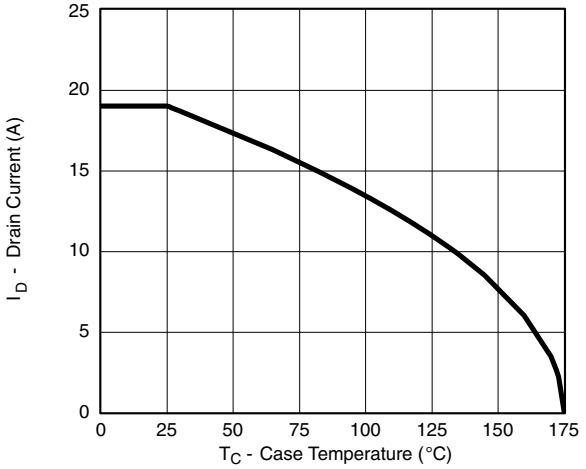


On-Resistance vs. Junction Temperature

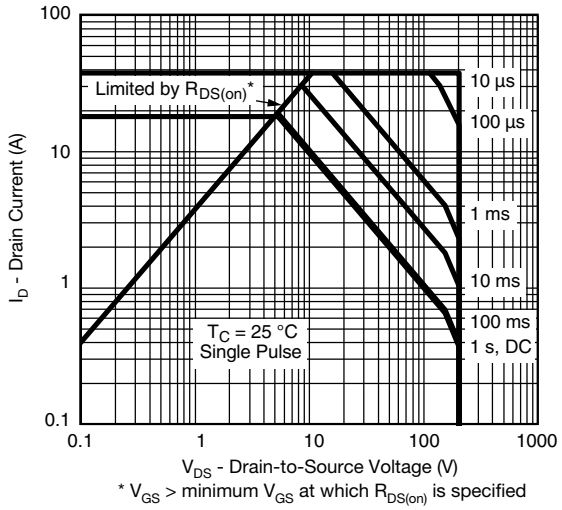


Source-Drain Diode Forward Voltage

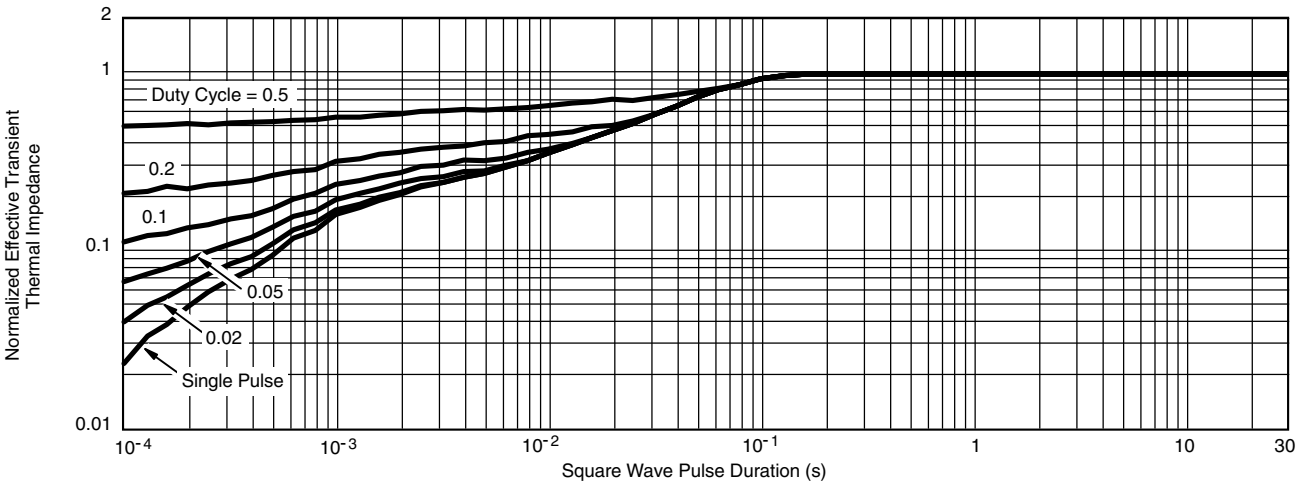
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature

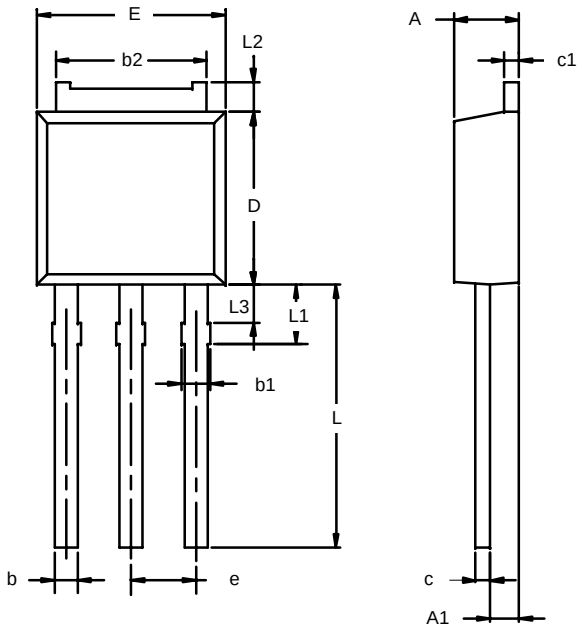


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-251AA



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	3.89	9.53	0.153	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060

Note: Dimension L3 is for reference only.

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